

IWGO 2026 Program Overview

Room /Time	Concourse	ESJ 0202
MoM		IWGO-MoM1: Plenary Session I IWGO-MoM2: Epitaxial Growth and Doping Control I
MoA		IWGO-MoA1: Defects Science I IWGO-MoA2: Defects Science II
MoP	Poster Sessions	
TuM		IWGO-TuM1: Substrate Development and Material Quality I IWGO-TuM2: Substrate Development and Material Quality II
TuA		IWGO-TuA1: Heterogeneous Integration and other WBG and UWBG Oxides Beyond Ga₂O₃ IWGO-TuA2: Defects Science III & Thermal Management
TuP	Poster Sessions	
WeM		IWGO-WeM1: Plenary Session II IWGO-WeM2: Epitaxial Growth and Doping Control II
WeA		IWGO-WeA: Advanced Device Scaling and Fabrication Techniques I
WeP	Poster Sessions	Rump Session (6:00 – 8:00 pm)
ThM		IWGO-ThM1: Theory, Modeling, and Simulation IWGO-ThM2: Defects Science IV
ThA	Offsite Excursion	
FrM		IWGO-FrM1: Plenary Session III IWGO-FrM2: Advanced Device Scaling and Fabrication Techniques II

Monday Morning, August 3, 2026

Room ESJ 0202		
8:00am	BREAKFAST	International Workshop on Gallium Oxide and Related Materials (IWGO-6) Session IWGO-MoM1 Plenary Session I Moderators: Marko Tadjer , U.S. Naval Research Laboratory, James Speck , University of California Santa Barbara
8:45am	Welcome & Sponsor Thank You	
9:00am	PLENARY: IWGO-MoM1-13 Single Crystals and Wafers of β -Ga ₂ O ₃ , β -(Al _x Ga _{1-x}) ₂ O ₃ , and r-GeO ₂ , Zbigniew Galazka , Leibniz-Institut für Kristallzüchtung, Germany	
9:45am	INVITED: IWGO-MoM1-22 Plasma-Treatment Based (Near) Surface Doping of Semiconducting Oxides, Oliver Bierwagen , Paul-Drude Institute for Solid State Electronics, Germany; Piero Mazzolini , University of Parma, Italy	
10:10am	INVITED: IWGO-MoM1-27 Lattice Defects in β -Ga ₂ O ₃ Crystals and Power Devices, Yongzhao Yao , Mie University, Japan	
10:35am	COFFEE BREAK	
11:05am	INVITED: IWGO-MoM2-38 Toward 150mm Ga ₂ O ₃ Epitaxy by HVPE, Jacob Leach , Caroline Reilly , Heather Splawn , KYMA TECHNOLOGIES, INC	International Workshop on Gallium Oxide and Related Materials (IWGO-6) Session IWGO-MoM2 Epitaxial Growth and Doping Control I Moderators: Oliver Bierwagen , Paul-Drude Institute for Solid State Electronics, Germany, Yuichi Oshima , National Institute for Materials Science, Japan
11:30am	IWGO-MoM2-43 MOCVD Growth of (011) β -Ga ₂ O ₃ up to 20 μ m: Defect Optimization and Device Impact, Md Mosarof Hossain Sarkar (Student) , Dong su Yu , The Ohio State University; Jiawei Liu , SUNY at Buffalo; Sadikul Alam , Mehidi Hassan , The Ohio State University; Yuki Ueda , Chia-Hung Lin , Kohel Sasaki , Novel Crystal Technology, Japan; Jinwoo Hwang , The Ohio State University; Uttam Singiseti , SUNY at Buffalo; Hongping Zhao , The Ohio State University	
11:45am	IWGO-MoM2-46 Colossal Bandgaps: Growing Si-Doped α -(Al _x Ga _{1-x}) ₂ O ₃ Films with $E_g \leq 7$ eV with s-MBE, Jacob Steele (Student) , Debaditya Bhattacharya , Kazuki Nomoto , Cornell University; M. K. Indika Senevirathna , Clark Atlanta University; Huili "Grace" Xing , Debbeep Jena , Darrell G. Schlom , Cornell University	
12:00pm	IWGO-MoM2-49 Fast Step-Flow Growth on Highly Offcut (100) Ga ₂ O ₃ Substrates, M Brooks Tellekamp , National Renewable Energy Laboratory; Drew Haven , David Joyce , Luxium Solutions; Henry Garland , John Mangum , National Renewable Energy Laboratory; Kevin Schulte , Anna Sacchi , Matthew Young , Andriy Zakutayev , national renewable Energy Laboratory	
12:15pm	IWGO-MoM2-52 Record High Mobility with Observation of Quantum Oscillations at Low Temperature for 2DEGs in MOCVD Grown β -(Al _x Ga _{1-x}) ₂ O ₃ / β -Ga ₂ O ₃ Heterostructures, Joshua Buontempo (Student) , Cameron Gorsak , Pushpanshu Tripathi , Hari Nair , Cornell University	

Monday Afternoon, August 3, 2026

Room ESJ 0202		
2:00pm	INVITED: IWGO-MoA1-1 Toward Quantitative Modeling of Temperature-Dependent Defect Physics in β -Ga ₂ O ₃ , <i>Elif Ertekin</i> , University of Illinois; <i>Michael Scarpulla</i> , University of Utah; <i>Joel Varley</i> , Lawrence Livermore National Lab; <i>Nasim Alem</i> , Penn State University; <i>Channyung Lee</i> , <i>Grace McKnight</i> , University of Illinois; <i>Aaditta Arnab</i> , University of Utah	International Workshop on Gallium Oxide and Related Materials (IWGO-6) Session IWGO-MoA1 Defects Science I Moderators: John Lyons , Naval Research Laboratory, Matthew McCluskey , Washington State University
2:25pm	IWGO-MoA1-6 Characterization of β -Ga ₂ O ₃ Deep Acceptor/n ⁻ Junction Diodes Grown by Molecular Beam Epitaxy, <i>Steve Rebollo (Student)</i> , <i>Wolfgang Buchmaier</i> , <i>Sriram Krishnamoorthy</i> , <i>James Speck</i> , UC Santa Barbara	
2:40pm	IWGO-MoA1-9 Identification and Suppression of Carbon-Related Trap States and Carrier Compensation in MOCVD-Grown β -Ga ₂ O ₃ , <i>Miranda Carver (Student)</i> , <i>Hemant Ghadi</i> , <i>Lingyu Meng</i> , <i>Dong Su Yu</i> , <i>Hongping Zhao</i> , <i>Aaron Arehart</i> , <i>Steven Ringel</i> , Ohio State University	
2:55pm	IWGO-MoA1-12 Deep Trap States in Mg/N Co-Implanted β -Ga ₂ O ₃ Current Blocking Layers Revealed by Thermally Stimulated Current Spectroscopy, <i>Hitoshi Takane</i> , <i>Yusuke Yamashita</i> , Toyota Central R&D Labs., Inc., Japan; <i>Fenfen Fenda Florena</i> , <i>Hironobu Miyamoto</i> , <i>Kohei Sasaki</i> , Novel Crystal Technology, Inc., Japan; <i>Daigo Kikuta</i> , Toyota Central R&D Labs., Inc., Japan	
3:10pm	IWGO-MoA1-15 Effects of 230 MeV Ca Swift Heavy Ion Irradiation on β -Ga ₂ O ₃ Schottky Diodes, <i>Yanzhen Zhao (Student)</i> , Ohio State University; <i>Cale Overstreet</i> , University of Tennessee, Knoxville; <i>Hemant Ghadi</i> , <i>Quentin Shuai</i> , Ohio State University; <i>Kay-Obbe Voss</i> , GSI Helmholtz Centre For Heavy Ion Research; <i>Maik Lang</i> , University of Tennessee, Knoxville; <i>Steven Ringel</i> , <i>Aaron Arehart</i> , Ohio State University	
3:25pm	IWGO-MoA1-18 Machine Learning Quantification of Dislocation Defects in Ga ₂ O ₃ Using X-Ray Topography, <i>James Gallagher</i> , NRL; <i>Christian Reimann</i> , Rigaku, Germany; <i>Caroline Reilly</i> , <i>Jacob Leach</i> , <i>Heather Splawn</i> , Kyma Technologies; <i>Nadeemullah Mahadik</i> , <i>Marko Tadjer</i> , <i>Karl Hobart</i> , <i>Michael Mastro</i> , NRL	
3:40pm	COFFEE BREAK	
4:10pm	INVITED: IWGO-MoA2-27 Advancing Understanding in Conductivity Control in Ga ₂ O ₃ Polymorphs and Alloys Through Atomistic Simulations, <i>Joel Varley</i> , Lawrence Livermore National Laboratory	International Workshop on Gallium Oxide and Related Materials (IWGO-6) Session IWGO-MoA2 Defects Science II Moderators: Emmanouil Kioupakis , University of Michigan, Hartwin Peelaers , University of Kansas
4:35pm	IWGO-MoA2-32 High-Throughput, High-Resolution, Three-Dimensional Observation of Threading Dislocations in β -Ga ₂ O ₃ Using Phase-Contrast Microscopy, <i>Yukari Ishikawa</i> , <i>Daiki Katsube</i> , Japan Fine Ceramics Center, Japan; <i>Yongzha Yao</i> , Mie Univ., Japan Fine Ceramics Center, Japan; <i>Koji Sato</i> , Japan Fine Ceramics Center, Japan; <i>Kohei Sasaki</i> , Novel Crystal Technology, Japan	
4:50pm	IWGO-MoA2-35 Origin of Donor Compensation in (Al _x Ga _(1-x)) ₂ O ₃ Alloys, <i>Sierra Seacat</i> , <i>Hartwin Peelaers</i> , University of Kansas	

International Workshop on Gallium Oxide and Related Materials (IWGO-6)

Room Concourse - Session IWGO-MoP

IWGO Poster Session I

5:30 – 7:30 pm

Moderators:

Esmat Farzana, Iowa State University,

Katie Gann, Naval Research Laboratory

IWGO-MoP-1 Anisotropic Wet Etching of β -Ga₂O₃ using TMAH, **Takayoshi Oshima**, NIMS, Japan

IWGO-MoP-2 Electrical Characterization of 1D P-N Heterojunctions with Axial and Core-Shell Architectures, **Roman Yatskiv**, Institute of Photonics and Electronics of the Czech Academy of Sciences, Czechia

IWGO-MoP-3 Enhancement of Breakdown Voltage in β -Ga₂O₃/NiO Heterojunction Diodes by Modulating p-NiO/p+NiO Widths, **SinSu Kyoung, SangHun Kim**, PowercubeseMI Inc., Republic of Korea

IWGO-MoP-4 Metal-Catalyst-Dependent Growth of β -Ga₂O₃ Nanowires on Sapphire for Solar-Blind UV Photodetectors, **JungBok Lee (Student)**, **MinSeok Jang, HeeJin Kim, JuEun An, HoJun Lee**, Pusan National University, Republic of Korea

IWGO-MoP-5 Epitaxial Growth of Si Doped β -(In_xGa_{1-x})₂O₃ Thin Films on (010) β -Ga₂O₃ Substrates, **Aoi Saito (Student)**, Kyoto Institute of Technology, Japan; **Hiroki Miyake**, MIRISE Technologies Corporation, Japan; **Hiroyuki Nishinaka**, Kyoto Institute of Technology, Japan

IWGO-MoP-6 Dependence of Substrate Orientation the β -Ga₂O₃ Single Crystal Layer Grown by the Flux Method, **Kentaro Ishida (Student)**, **Toshinori Taishi**, Shinshu University, Japan

IWGO-MoP-7 Characterization of β -Ga₂O₃ Epitaxial Layers Using Time-Resolved Photoluminescence, **Mahiro Ishikawa (Student)**, **Takuma Ishihara, Kazuki Shimazoe**, Nagoya Institute of Technology, Japan; **Kahei Sasaki**, Novel Crystal Technology, Japan; **Masashi Kato**, Nagoya Institute of Technology, Japan

IWGO-MoP-8 Crack-Free Dicing of β -Ga₂O₃ Substrates, **Michael Liao**, APEX Microdevices; **Mark Goorsky**, University of California Los Angeles; **Piyush Shah**, APEX Microdevices

IWGO-MoP-9 Silicon Implantation Doping for Channel Definition of UID Alpha and Beta Ga₂O₃ Lateral MESFET Transistors, **Aniol Vellvehi i Lovet (Student)**, Institut de microelectrònica de Barcelona (IMB-CNM-CSIC), Spain; **Amador Perez Tomas Perez Tomas**, Institut de Microelectrònica de Barcelona (IMB-CNM-CSIC), Spain

IWGO-MoP-10 Temperature-dependent Characteristics of HVPE-grown β -Ga₂O₃ Schottky Contacts with Different Metals, **Eito Hatayama (Student)**, **Kazutaka Kanegae, Hajime Takayama, Michihiro Shintani, Hiroyuki Nishinaka**, Kyoto Institute of Technology, Japan

IWGO-MoP-11 Effect of Ion Charge and Implantation Dosage on Damage Recovery and Band Gap Narrowing in Sn-Implanted β -Ga₂O₃, **Kishor Upadhyaya**, KAUST, Saudi Arabia; **D.M. Esteves, Marco Peres, Katharina Lorenz**, Instituto Superior Técnico, Portugal; **Iman Roqan**, KAUST, Saudi Arabia

IWGO-MoP-12 Electrical Stability of Cr₂O₃/ β -Ga₂O₃ Heterojunction Diodes (HJDs) with Orientation-Dependent Breakdown Electric Field, **Yizheng Liu (Student)**, **Haochen Wang, Carl Peterson, Chinmoy Saha, James Speck, Chris Van de Walle, Sriram Krishnamoorthy**, University of California at Santa Barbara

IWGO-MoP-13 Direct Atomic Layer Processing (DALP®): Spatially Localized, Multi-Material Fabrication for Next-Generation Devices from Discovery to Manufacturing, **Mira Baraket**, ATLANT 3D Nanosystems, Denmark

IWGO-MoP-14 NiO/Ga₂O₃ Heterojunction Rectifiers with Reverse Breakdown Voltage > 8.1 kV, **Hsiao-Hsuan Wan, Jian-Sian Li, Chao-Ching Chiang, Katharina Loske (Student)**, **Travis Anderson**, University of Florida; **Aman Haque**, The Pennsylvania State University; **Marko Tadjer**, Naval Research Laboratory, USA; **Jacob Leach, Caroline Reilly**, Kyma Technologies; **Fan Ren**, University of Florida

IWGO-MoP-15 P-Type LiyNi_{1-x}MyMg_xO for β -Ga₂O₃ Heterojunction Power Device Applications, **Madani Labeled**, **You Seung Rim**, Sejong University, Republic of Korea

IWGO-MoP-16 Multi-Kilovolt Vertical Nio/Ga₂O₃ P-N Heterojunction Diodes with Ring-Assisted Junction Termination Extension, **Kanghee Shin (Student)**, Sejong University, Republic of Korea; **Ho Jung Jeon**, Seoul National University, Republic of Korea; **Jang Hyeok Park, Madani Labeled, You Seung Rim**, Sejong University, Republic of Korea

IWGO-MoP-17 Wafer-Scale Heteroepitaxy of Sn-Alloyed ϵ -Ga₂O₃ on Sapphire via Low-Pressure Mist-CVD, **Yan Wang (Student)**, **Chee Keong Tan**, Hong Kong University of S&T (GZ), China

IWGO-MoP-18 MOCVD-grown 12 μ m Thick Sn Doped (001) β -Ga₂O₃ Layers with Extremely Low Free Charge Concentrations, **Akash Patnaik**, UVSQ – CNRS, France; **Corinne Sartet**, UVSQ – CNRS, France; **Yunlin Zheng**, INSP, Sorbonne Université, France; **Thomas Ribault, Yves Dumont, Ekaterine Chikoidze**, UVSQ – CNRS, France

IWGO-MoP-19 Structural Properties of Mist CVD Grown Rutile GeO₂ Thin Films on TiO₂ Substrates, **Kazuki Shimazoe, Shota Ishiyama**, Nagoya Institute of Technology, Japan; **Hiroyuki Nishinaka**, Kyoto Institute of Technology, Japan; **Masashi Kato**, Nagoya Institute of Technology, Japan

IWGO-MoP-20 Epitaxy of b-(Al_xGa_{1-x})₂O₃ on (001) b-Ga₂O₃ Substrates by MOCVD, **Indraneel Sanyal**, AIXTRON Ltd., UK; **Dan Lamb, Ciaran Llewelyn, Shreyasi Maitra, Saptarsi Ghosh**, Swansea University, UK; **Andrew Pakes, K.B.K Teo**, AIXTRON Ltd., UK

IWGO-MoP-21 Performance Enhancement of β -Ga₂O₃ Deep-Ultraviolet Photodetectors via Al₂O₃ Passivation, **Hee Won Shin (Student)**, **Jang Hyeok Park, You Seung Rim**, Sejong University, Republic of Korea; **Si-Young Bae**, Pukyong National University, Republic of Korea

IWGO-MoP-22 Suppression of Twin Nucleation in Bulk β -Ga₂O₃ Using Wide-Width Seeds, **Won-Jae LEE**, Dong-Eui University, Republic of Korea; **Eun-Seo LEE (Student)**, Dong Eui University, Republic of Korea; **Eun-Jeong An, Sang-Jin Bae, Ho-Gyun Yun, Jung-Gon Kim, Kwang-Hee Jung, Mi-Seon Park**, Dong-Eui University, Republic of Korea; **Dong-Jin Lee, Jin-Ki Kang**, AXEL, Republic of Korea

IWGO-MoP-23 Comparison of NiO/ β -Ga₂O₃ Heterojunction Diodes Fabricated Using Planar and Confocal RF Magnetron Sputtering Systems, **Wojciech Hendelek (Student)**, Łukasiewicz Research Network-Institute of Microelectronics and Photonics, Warsaw University of Technology- Institute of Microelectronics and Optoelectronics, Poland; **Aleksandra Wójcicka**, Łukasiewicz Research Network-Institute of Microelectronics and Photonics, Warsaw University of Technology- Institute of Microelectronics and Optoelectronics, Poland; **Aneta Gołębiewska**, Łukasiewicz Research Network-Institute of Microelectronics and Photonics, Poland; **Jarosław Tarenko, Oskar Sadowski, Maciej Kamiński**, Łukasiewicz Research Network-Institute of Microelectronics and Photonics, Warsaw University of Technology - Institute of Microelectronics and Optoelectronics, Poland; **Marcin Guza, Marek Wzorek**, Łukasiewicz Research Network-Institute of Microelectronics and Photonics, Poland; **Justyna Wierzbicka**, Łukasiewicz Research Network-Institute of Microelectronics and Photonics, Warsaw University of Technology - Institute of Microelectronics and Optoelectronics, Poland; **Krzysztof Czuba, Anna Szerling, Andrzej Taube**, Łukasiewicz Research Network-Institute of Microelectronics and Photonics, Poland

IWGO-MoP-24 A Non-Van Der Waals Platform for Deep-Subwavelength Twist-Polaritonics Based on β -Ga₂O₃ Nanoflakes, **Debo Hu**, National Center for Nanoscience and Technology, China

IWGO-MoP-25 Engineering Considerations for the Growth of Sb-Doped Sn_{0.4}Ge_{0.6}O₂ Thin Films, **Avery-Ryan Ansbro (Student)**, **Yi Liang, Pat Kezer, Manasi Londhe, John Heron**, University of Michigan, Ann Arbor

IWGO-MoP-26 Characterization and Light Emission of CBLs with Varying Nitrogen Implantation Doses for β -Ga₂O₃ Devices, **Kohei Ebihara, Tetsuro Hayashida, Munetaka Noguchi, Rina Tanaka, Ryuji Sakai, Hiroshi Watanabe, Masaki Taya, Tatsuro Watahiki**, Mitsubishi Electric Corporation, Japan

IWGO-MoP-27 Homoepitaxial Growth of β -Ga₂O₃ Using a Novel High-Density Oxygen Radical Source (HD-ORS) for MBE and PVD, **Arun Kumar Dhasiyan**, Nagoya University, Japan; **Tomoki Takeda, Naofumi Kato**, NU-Rei Co., Ltd, Japan; **Naahiro Shimizu, Osamu Oda, Masaru Hari**, Nagoya University, Japan

IWGO-MoP-28 Lock-in Infrared Thermography Techniques for Thermal Characterization of Ultra-Wide Bandgap Semiconductors, **Ethan Scott, Jessica Reyes**, University of Virginia; **Jeffrey Braun, John Gaskins**, Laser Thermal; **Marko Tadjer**, Naval Research Laboratory; **Patrick Hopkins**, University of Virginia

IWGO-MoP-29 Reverse Leakage Reduction of β -Ga₂O₃ Schottky Barrier Diode by Ex-Situ Mg Annealing Diffusion, **Zhiyu Xu, Jia Wang, Haitao Wang, Hiroshi Amano**, Nagoya University, Japan

IWGO-MoP-30 In-situ Reflectometry for Monitoring Growth Rate, Surface Morphology, and Doping in MOVPE Homoepitaxy of β -Ga₂O₃, **Kolja Haberland**, LayTec AG, Germany; **Ta-Shun Chou**, NextGO Epi UG, Germany; **Andreas Fiedler, Andreas Popp, Saud Bin Anooz, Raimund Grüneberg, Jana Rehm, Arub Akhtar**, Institut für Kristallzüchtung IKZ, Germany

IWGO-MoP-31 Epitaxial β -(Al_xGa_{1-x})₂O₃ Thin Films Grown on (100) β -Ga₂O₃ by MOVPE, **Deborah Kern (Student)**, **Martin Handwerg, Ta-Shun Chou, Saud Bin Anooz, Martin Schmidbauer, Andreas Popp, Andreas Fiedler**, Leibniz Institute for Crystal Growth, Germany

IWGO-MoP-32 NiO/ β -Ga₂O₃ Vertical Pin Diodes with Low Leakage and Size Dependent Transport Characteristics, *Tom Micottis (Student)*, Institute of Electronics, Microelectronics and Nanotechnology (IEMN), France

IWGO-MoP-33 Electronic and Electrical Properties of Mg_xNi_{1-x}O Thin Films Deposited by Rf Magnetron Sputtering, *Harunobu Yasuda (Student)*, *Shunya Matsui*, *Takayuki Akiba*, *Tomohiro Yamaguchi*, *Tohru Honda*, Department of Electrical Engineering and Electronics, Graduate School of Engineering, Kogakuin University, Japan; *Hironobu Miyamoto*, *Kohei Sasaki*, Novel Crystal Technology, Japan; *Takeyoshi Onuma*, Department of Electrical Engineering and Electronics, Graduate School of Engineering, Kogakuin University, Japan

IWGO-MoP-34 Improved Structural and Electrical Properties of MOCVD-Grown β -Ga₂O₃/Sapphire Films with Compositionally-Graded (Al_xGa_{1-x})₂O₃ Buffer, *Filip Guemann*, *Sai Gurukrishna Vadlamudi*, *Kristina Hušeková*, *Edmund Dobročka*, *Peter Nádaždy*, *Dagmar Gregušová*, *Iryna Kozak*, *Ondrej Pohorelec*, Institute of Electrical Engineering, Slovak Academy of Sciences, Slovakia; *Matej Mičušík*, Polymer Institute, Slovak Academy of Sciences, Slovakia; *Igor Piš*, *Milan Ťapajna*, Institute of Electrical Engineering, Slovak Academy of Sciences, Slovakia

IWGO-MoP-35 Reduction of Si Impurities in β -Ga₂O₃ Homoepitaxial Films Grown by Mist-CVD, *Yuki Isobe (Student)*, Kyoto University, Japan; *Yuki Yamamoto*, OXIDE Corporation, Japan; *Hirokazu Izumi*, Hyogo Prefectural Institute of Technology, Japan; *Takeru Wakamatsu*, Kyoto University, Japan; *Kentaro Kaneko*, Ritsumeikan University, Japan; *Shizuo Fujita*, *Katsuhisa Tanaka*, Kyoto University, Japan

IWGO-MoP-36 Prospects of Safe and Cost-Effective Mist CVD for Homoepitaxial Growth and Devices of β -Ga₂O₃, *Shizuo Fujita*, *Takeru Wakamatsu*, *Yuki Isobe*, *Hikaru Ikeda*, Kyoto University, Japan; *Yuji Ando*, *Hidemasa Takahashi*, *Ryutarō Makisako*, Nagoya University, Japan; *Tetsuzo Ueda*, Panasonic, Japan; *Jun Suda*, *Katsuhisa Tanaka*, Kyoto University, Japan; *Hidetaka Sugaya*, Panasonic, Japan

IWGO-MoP-37 Quaternary (Al_xSc_yGa_{1-x-y})₂O₃ for Lattice-Matched β -Ga₂O₃ Heterostructures, *Kazuki Koreishi (Student)*, Institute of Science Tokyo, Japan; *Kodai Niitsu*, National Institute for Materials Science, Japan; *Takuto Soma*, Tohoku University, Japan; *Kohei Yoshimatsu*, *Akira Ohtomo*, Institute of Science Tokyo, Japan

IWGO-MoP-38 Photoemission Electron Microscopy for Imaging Defects, *Andrew Winchester*, *Min-Yeong Kim*, *Ory Maimon*, National Institute for Science and Technology (NIST); *Dinusha Mudiyansele*, *Houqiang Fu*, Arizona State University; *Sang-Mo Koo*, Kwangwoon University, Republic of Korea; *Qiliang Li*, George Mason University; *Sujitra Pookpanratana*, National Institute for Science and Technology (NIST)

IWGO-MoP-39 First-Principles and Thermodynamic Study of (Al_xGa_{1-x})₂O₃ Growth by PA-MBE, *Rie Togashi*, Sophia University, Japan; *Akira Kusaba*, Kyushu University, Japan; *Masataka Higashiwaki*, Osaka Metropolitan University/NICT, Japan; *Yoshinao Kumagai*, Tokyo University of Agriculture and Technology, Japan

IWGO-MoP-40 Benchmarking Gate Charge in Gallium Oxide Transistors, *Daniel Dryden*, Air Force Research Laboratory

IWGO-MoP-41 Defect Characterization of Czochralski Grown Gallium Oxide, *Aleksander Imhof*, *Nadeemullah Mahadiq*, Naval Research Laboratory; *Marko Tadjer*, naval research Laboratory; *Robert Lavelle*, Pennsylvania State University

IWGO-MoP-42 Adsorption Controlled Growth and Doping of α -(Al,Ga)₂O₃ by Suboxide Molecular Beam Epitaxy, *Sushma Raghuvansy*, *Marco Schowalter*, *Alexander Karg*, *Martin Samuel Williams*, *Manuel Alonso-Orts*, *Andreas Rosenauer*, *Martin Eickhoff*, University of Bremen, Germany; *Patrick Vogt*, Paul-Drude-Institut für Festkörperelektronik Leibniz-Institut im Forschungsverbund Berlin, Germany

Tuesday Morning, August 4, 2026

Room ESJ 0202		
8:00am	BREAKFAST	International Workshop on Gallium Oxide and Related Materials (IWGO-6) Session IWGO-TuM1 Substrate Development and Material Quality I Moderators: Masataka Higashiwaki , Osaka Metropolitan University/NICT, Japan, Yoshinao Kumagai , Tokyo University of Agriculture and Technology, Japan
8:30am	INVITED: IWGO-TuM1-7 Invited Paper, <i>Lynn Petersen</i> , Office of Naval Research	
8:55am	INVITED: IWGO-TuM1-12 Cost Analysis of Gallium Oxide Wafer Production and Challenges and Strategies for Cost Reduction, <i>Akito Kuramata</i> , <i>Takuya Igarashi</i> , <i>Shinya Watanabe</i> , Novel Crystal Technology, Inc., Japan; <i>Chia-Hung Lin</i> , Novel Crystal Technology, Inc., Taiwan; <i>Kohei Sasaki</i> , <i>Kimiyooshi Koshi</i> , Novel Crystal Technology, Inc., Japan	
9:20am	INVITED: IWGO-TuM1-17 Dawn of a 7 eV Semiconductor: Si-doped α -(Al _x Ga _{1-x}) ₂ O ₃ , <i>Darrell Schlom</i> , Cornell University	
9:45am	IWGO-TuM1-22 Demonstration of 150 mm (001) β -Ga ₂ O ₃ Substrates Grown by EFG Method, <i>Sho Hasegawa</i> , <i>Kimiyooshi Koshi</i> , <i>Yuki Ueda</i> , <i>Ryoichi Sakaguchi</i> , Novel Crystal Technology, Inc., Japan; <i>Isao Sakamoto</i> , Novel Crystal Technology, Inc, Japan; <i>Keita Konishi</i> , <i>Makoto Mizui</i> , <i>Yu Yamaoka</i> , <i>Shinya Watanabe</i> , <i>Kohei Sasaki</i> , <i>Akito Kuramata</i> , Novel Crystal Technology, Inc., Japan	
10:00am	IWGO-TuM1-25 Bulk Single Crystal Growth of β -Ga ₂ O ₃ with Automatic Diameter Control System Specialized for the OCCC Method, <i>Masanori Kitahara (Student)</i> , <i>Taketoshi Tomida</i> , FOX Corporation, Japan; <i>Vladimir Kochurikhin</i> , <i>Gushchina Liudmila</i> , C&A Corp, Russian Federation; <i>Yasuhiro Shoji</i> , <i>Kei Kamada</i> , FOX Corporation, Japan; <i>Koichi Kakimoto</i> , Tohoku University, Japan; <i>Akira Yoshikawa</i> , FOX Corporation, Japan	
10:15am	IWGO-TuM1-28 Development of High-Quality 4" β -Ga ₂ O ₃ (010) Wafer via the VB Method, <i>Yuki Yamamoto</i> , <i>Shigenori Shimizu</i> , OXIDE, Japan; <i>Kensuke Mizukoshi</i> , <i>Takashi Nishinoiri</i> , Ceratec Japan Co., Ltd., Japan; <i>Toshinori Taishi</i> , <i>Keigo Hoshikawa</i> , Shinshu Univ., Japan	
10:30am	COFFEE BREAK	
11:00am	INVITED: IWGO-TuM2-37 Defect Complexes and β -to- γ Phase Boundaries in Si-implanted Ga ₂ O ₃ , <i>Naomi Pieczulewski (Student)</i> , <i>Katie Gann</i> , Cornell University; <i>Thaddeus Asef</i> , <i>Brenton Noesges</i> , Air Force Research Laboratory, Materials and Manufacturing Directorate, USA; <i>Michael Thompson</i> , <i>David Muller</i> , Cornell University	International Workshop on Gallium Oxide and Related Materials (IWGO-6) Session IWGO-TuM2 Substrate Development and Material Quality II Moderators: Zbigniew Galazka , Leibniz Institute for Crystal Growth, Germany, Kohei Sasaki , Novel Crystal Growth, Japan
11:25am	IWGO-TuM2-42 Thulium-doped Gallium Oxide Scintillators: Growth and Characterization, <i>Marko Tadjer</i> , <i>Lee Mitchell</i> , Naval Research Laboratory; <i>Robert Lavelle</i> , Pennsylvania State University Applied Research Laboratory; <i>Alex Lebedinsky</i> , University of Houston; <i>Darshana Wickramaratne</i> , <i>Evan Glaser</i> , Naval Research Laboratory; <i>Katie Gann</i> , <i>Tia Gray</i> , National Research Council; <i>Alan Jacobs</i> , <i>James Spencer Lundh</i> , <i>Steven Bennett</i> , Naval Research Laboratory; <i>Matthew Krohn</i> , Pennsylvania State University Applied Research Laboratory; <i>Bernard Philips</i> , Naval Research Laboratory; <i>Kumar Saurabh</i> , <i>P. Shiv Halasyamani</i> , University of Houston; <i>Karl Hobart</i> , Naval Research Laboratory	
11:40am	IWGO-TuM2-45 Growth of β -Ga ₂ O ₃ Crystals by Plling-Down EFG Method with a Raw Material Supply System, <i>Yuki Ueda</i> , Novel Crystal Technology Inc., Japan; <i>Kimiyooshi Koshi</i> , <i>Sho Hasegawa</i> , <i>Kohei Sasaki</i> , <i>Akito Kuramata</i> , Novel Crystal Technology, Inc., Japan	
11:55am	IWGO-TuM2-48 Redefining β -Ga ₂ O ₃ Smart Cut™ Through Optimized Ion Implantation, <i>Adrien Roth (Student)</i> , <i>Guillaume Gelineau</i> , <i>Lucas Colonel</i> , <i>Frédéric Mazen</i> , <i>Frédéric Milési</i> , <i>Florence Madeira</i> , <i>Nicolas Troutot</i> , CEA-Leti, France; <i>David Eon</i> , CNRS, France; <i>Julie Widiez</i> , CEA-Leti, France	
12:10pm	IWGO-TuM2-51 HCl-based Halide Vapor Phase Epitaxy and HCl Gas Etching on (-112) β -Ga ₂ O ₃ Substrates, <i>Takayoshi Oshima</i> , <i>Yuichi Oshima</i> , NIMS, Japan	

Tuesday Afternoon, August 4, 2026

Room ESJ 0202		
2:00pm	INVITED: IWGO-TuA1-1 Heterogeneous Gallium Oxide Integration and Vertical Device Technology, <i>Martin Kuball</i> , University of Bristol, UK	International Workshop on Gallium Oxide and Related Materials (IWGO-6) Session IWGO-TuA1 Heterogeneous Integration and other WBG and UWBG Oxides Beyond Ga₂O₃ Moderators: Andrew Green, AFRL, Man Hoi Wong, The Hong Kong University of Science and Technology, Hong Kong
2:25pm	IWGO-TuA1-6 >10 kV Vertical NiO _x /(011) β-Ga ₂ O ₃ HJDs with PFOM >2.3 GW/cm ² , <i>Yizheng Liu (Student)</i> , Carl Peterson, Chinmoy Saha, University of California at Santa Barbara; <i>Marko Tadjer</i> , Naval Research Laboratory; <i>Sriram Krishnamoorthy</i> , University of California at Santa Barbara	
2:40pm	IWGO-TuA1-9 Semiconductor Properties of Epitaxial NiGa ₂ O ₄ Spinel That Forms at Ga ₂ O ₃ /NiO Interfaces, <i>Kingsley Egbo</i> , <i>Anna Sacchi</i> , <i>M. Brooks Tellekamp</i> , <i>Andriy Zakutayev</i> , National Laboratory of the Rockies	
2:55pm	IWGO-TuA1-12 Breaking the 6 eV Barrier: Colossal Bandgap Electronics with Si Doped α-(Al _x Ga _{1-x}) ₂ O ₃ by S-MBE, <i>Debaditya Bhattacharya (Student)</i> , <i>Jacob Steele</i> , <i>Kazuki Nomoto</i> , <i>Naomi Pieczulewski</i> , Cornell University; <i>Preston Sorensen</i> , University of Nebraska - Lincoln; <i>Madhav Ramesh</i> , Cornell University; <i>Indika Senevirathna</i> , Clark Atlanta University; <i>Mathias Schubert</i> , University of Nebraska - Lincoln; <i>David Muller</i> , <i>Huili Grace Xing</i> , <i>Darrell Schlom</i> , <i>Debdeep Jena</i> , Cornell University	
3:10pm	IWGO-TuA1-15 Thin-Film β-Ga ₂ O ₃ Composite Substrates for Thermal Management Solutions, <i>Michael Liao</i> , APEX Microdevices; <i>Mark Goorsky</i> , University of California Los Angeles; <i>Piyush Shah</i> , APEX Microdevices	
3:25pm	COFFEE BREAK	
3:55pm	IWGO-TuA2-24 Conductive Al ₂ O ₃ with Ohmic Contacts via Ion Implantation, <i>Alan Jacobs</i> , <i>Katie Gann</i> , <i>James Lundh</i> , <i>Daniel Pennachio</i> , <i>Darshana Wickramaratne</i> , <i>Karl Hobart</i> , <i>Michael Mastro</i> , Naval Research Laboratory	International Workshop on Gallium Oxide and Related Materials (IWGO-6) Session IWGO-TuA2 Defects Science III & Thermal Management Moderators: Martin Kuball , University of Bristol, UK, Heather Splawn , KYMA TECHNOLOGIES, INC.
4:10pm	IWGO-TuA2-27 In-Situ X-Ray Topography Observation of Behavior of Dislocations in β-Ga ₂ O ₃ (001) Schottky Barrier Diode During Applying Voltage, <i>Daiki Katsube</i> , Japan Fine Ceramics Center, Japan; <i>Yongzhao Yao</i> , Mie University, Japan; <i>Daiki Wakimoto</i> , <i>Hironobu Miyamoto</i> , <i>Kohei Sasaki</i> , <i>Akito Kuramata</i> , Novel Crystal Technology, Japan; <i>Yukari Ishikawa</i> , Japan Fine Ceramics Center, Japan	
4:25pm	IWGO-TuA2-30 Killer Defects in (011) HVPE-Grown β-Ga ₂ O ₃ Schottky Barrier Diodes Studied by Synchrotron X-ray Topography and Emission Microscopy, <i>Masanori Eguchi</i> , Synchrotron Light Application Center, Saga University, Japan; <i>Shotaro Nakaniwa</i> , <i>Makoto Sato</i> , <i>Niloy Chandra Saha</i> , Department of Electrical and Electronic Engineering, Saga University, Japan; <i>Chia-Hung Lin</i> , <i>Kohei Sasaki</i> , Novel Crystal Technology, Japan; <i>Makoto Kasu</i> , Department of Electrical and Electronic Engineering, Saga University, Japan	
4:40pm	IWGO-TuA2-33 Impact of Bias Dependent Joule Heating on Gallium Oxide Lateral Transistors via Deep UV Thermal Imaging, <i>Dominic Myren (Student)</i> , University of Connecticut; <i>Daniel Dryden</i> , Air Force Research Laboratory; <i>Cameron Gorsak</i> , <i>Hari Nair</i> , Cornell University; <i>Ahmad Islam</i> , <i>Andrew Green</i> , Air Force Research Laboratory; <i>Georges Pavlidis</i> , University of Connecticut	
4:55pm	IWGO-TuA2-36 Engineered Substrates for Ga ₂ O ₃ Vertical Power Devices, <i>Caroline Reilly</i> , Kyma Technologies, Inc.; <i>Sean O'Leary</i> , Modern Microsystems, Inc.; <i>Emma Rocco</i> , US Naval Research Laboratory; <i>Craig McGray</i> , Modern Microsystems, Inc.; <i>Marko Tadjer</i> , <i>Karl Hobart</i> , US Naval Research Laboratory; <i>Heather Splawn</i> , <i>Jacob Leach</i> , Kyma Technologies, Inc.	

International Workshop on Gallium Oxide and Related Materials (IWGO-6)

Room Concourse - Session IWGO-TuP

IWGO Poster Session II

5:30pm

Moderators:

A F M Anhar Uddin Bhuiyan, University of Massachusetts Lowell,
Nidhin Kurian Kalarickal, Arizona State University,

IWGO-TuP-1 Observation of the 2 eV Defect in Nitrogen Doped Ga₂O₃ by DLTS, *Jian Li*, Core4ce LLC; *Brenton Noesges*, *Prescott Evans*, Air Force Research Laboratory, Materials and Manufacturing Directorate, USA; *Jacob Breakfield*, *Zach Weber*, *Nolan Hendricks*, *Andy Green*, Air Force Research Laboratory; *Adam Neal*, *Tadj Asel*, *Shin Mou*, Air Force Research Laboratory, Materials and Manufacturing Directorate, USA

IWGO-TuP-2 Cathodoluminescence Study of Rutile GeO₂ Grown via Mist CVD, *Kazuki Shimazoe*, *Shota Ishiyama*, Nagoya Institute of Technology, Japan; *Kazutaka Kanegae*, *Hiroyuki Nishinaka*, Kyoto Institute of Technology, Japan; *Masashi Kato*, Nagoya Institute of Technology, Japan

IWGO-TuP-3 Temperature Dependent Switching Characteristics of p-NiO/β-Ga₂O₃ Heterojunction Mosfets Under Cryogenic Conditions, *Joonhui Park*, *Taejun Park*, *Yusup Jung*, *Taiyoung Kang*, *Sinsu Kyoung*, PowerCubeSemi. Inc., Republic of Korea

IWGO-TuP-4 Influence of Sapphire Substrate Orientation on Epitaxial Rutile GeO₂ Thin Film Solar-Blind Photodetector Properties, *Eriks Dipans (Student)*, *Edwards Strods*, *Sven Oras*, *Annamarija Trausa*, *Jevgenijs Gabrusenoks*, *Edgars Butanovs*, Institute of Solid State Physics, University of Latvia

IWGO-TuP-5 Effect of Unintentional Si Impurities on F-doped β-Ga₂O₃ Thin Films Grown by Mist CVD, *Ichiro Seike (Student)*, Kyoto Institute of Technology, Japan; *Hiroki Miyake*, MIRISE Technologies Corporation, Japan; *Hiroyuki Nishinaka*, Kyoto Institute of Technology, Japan

IWGO-TuP-6 First Demonstration of p-type LiGa₅O₈ UWBG Thin Films by MOCVD, *Dong Su Yu (Student)*, *Mingxuan Wu*, *Binzhi Liu*, *Md Mosarof Hossain Sarkar*, *Kaitian Zhang*, *Jinwoo Hwang*, *Hongping Zhao*, The Ohio State University

IWGO-TuP-7 Fabrication and Characteristics of α-Ga₂O₃-Based Schottky Barrier Diodes on Sapphire Substrates for Microwave Rectenna Applications, *Takeru Wakamatsu*, Kyoto University, Japan; *Yasuo Ohno*, Laser Systems Inc., Japan; *Hikaru Ikeda*, *Shizuo Fujita*, Kyoto University, Japan; *Tomomi Hiraoka*, Laser Systems Inc., Japan; *Kentaro Kaneko*, Ritsumeikan University, Japan; *Katsuhisa Tanaka*, Kyoto University, Japan

IWGO-TuP-8 Gigantic Space Charge Limited Currents and Thermal Effects in Si-Fe-doped Ga₂O₃ Devices, *Pierre Gallarday (Student)*, *Aniol Vellvehi*, INSTITUT OF MICROELECTRONICS OF BARCELONA - (IMB-CNM-CSIC), Spain; *Verena Leitgeb*, Department Microelectronics, Materials Center Leoben Forschung GmbH (MCL), Austria; *Miquel Vellvehi*, *Josep Montserrat*, INSTITUT OF MICROELECTRONICS OF BARCELONA - (IMB-CNM-CSIC), Spain; *Barbara Kosednar-Legenstein*, *Lisa Mitterhuber*, *Elke Kraker*, *Anton Köck*, Department Microelectronics, Materials Center Leoben Forschung GmbH (MCL), Austria; *José Rebollo*, *Amador Pérez-Tomás*, INSTITUT OF MICROELECTRONICS OF BARCELONA - (IMB-CNM-CSIC), Spain

IWGO-TuP-9 Conductive Si-doped β-Ga₂O₃ by Atomic Layer Deposition and Annealing, *Katie Gann*, *Benjamin Greenberg*, *Daniel Pennachio*, Naval Research Laboratory; *Jeffrey Woodward*, Naval research Laboratory; *Alan Jacobs*, *Emma Rocco*, *Boris Feygelson*, *Rachael Myers-Ward*, *Karl Hobart*, *Michael Mastro*, Naval Research Laboratory

IWGO-TuP-10 Atomic Scale Investigation of (100) Twin Boundary in EFG-Grown Sn-Doped β-Ga₂O₃, *Mehidi Hassan (Student)*, *Binzhi Liu*, *Jinwoo Hwang*, Ohio State University

IWGO-TuP-11 Optimized CMP Processing and Subsurface Damage Control for High-Quality (010) β-Ga₂O₃ Single Crystals, *Won-Jae Lee*, *Eun-Jeong An (Student)*, *Eun-Seo Lee*, *Sang-Jin Bae*, *Ho-Gyun Yun*, *Kwang-Hee Jung*, *Jung-Gon Kim*, *Mi-Seon Park*, Dong-eui university, Busan, Republic of Korea; *Jin-Ki Kang*, *Dong-Jin Lee*, *Axel*, Republic of Korea

IWGO-TuP-12 Heat-resistant Characteristics of Li doped NiO Films Deposited by RF Magnetron Sputtering, *Shunya Matsui (Student)*, *Harunobu Yasuda*, *Tomohiro Ymaguchi*, *Tohru Honda*, Department of Electrical Engineering and Electronics, Kogakuin University, Japan; *Hironobu Miyamoto*, *Kohei Sasaki*, Novel Crystal Technology, Japan; *Takeyoshi Onuma*, Department of Electrical Engineering and Electronics, Kogakuin University, Japan

IWGO-TuP-13 Heavy-Ion Microprobe Induced Parasitic Channel in Ga₂O₃ MOSFETs, *Adam Neal*, Air Force Research Laboratory, Materials and Manufacturing Directorate, USA; *Daram Ramdin*, Core4ce; *Eric O'Quinn*, University of Tennessee Knoxville; *Adam Charnas*, Air Force Research Laboratory, Materials and Manufacturing Directorate, USA; *Kay-Obbe Voss*, GSI Helmholtzzentrum für Schwerionenforschung, Germany; *Cale Overstreet*, University of Tennessee Knoxville; *Cameron Gorsak*, *Hari Nair*, Cornell University; *Andrew Green*, Air Force Research Laboratory, Sensors Directorate; *Thaddeus Asel*, *Shin Mou*, Air Force Research Laboratory, Materials and Manufacturing Directorate, USA; *Maik Lang*, University of Tennessee Knoxville

IWGO-TuP-14 Large-Area, UVC Passive Pixel Sensors based on Heteroepitaxial β-Ga₂O₃, *Hyoljung Kim (Student)*, *SiSung Yoon*, *GeonWook Yoo*, Soongsil University, Republic of Korea

IWGO-TuP-15 Heteroepitaxial Growth of β-Ga₂O₃ on High-Angle Off-Cut Sapphire via MOCVD: Optimization through Minimum Oxygen Distance Simulations, *Hyeong-Yun Kim (Student)*, *JungHun Choi*, *Ji-Hyeon Park*, *Dae-woo Jeon*, Korea Institute of Ceramic Engineering and Technology, Republic of Korea

IWGO-TuP-16 Defect- and Dopant-engineered p-type Conductivity in Epitaxial ZnGa₂O₄ Spinel Oxide Thin Films, *Mohammad M. Afandi*, *Young Min Park*, *Gyeong Ryul Lee*, *Roy B. Chung*, Kyungpook National University, Republic of Korea

IWGO-TuP-17 Remote Epitaxy of α-Ga₂O₃ via Polycrystalline MoS₂, *Gyeong Ryul Lee (Student)*, *Young Min Park*, *Roy Chung*, Kyungpook National University, Republic of Korea

IWGO-TuP-18 β-Ga₂O₃ Growth on Single Crystal Diamond (111), *Arpit Nandi*, University of Bristol, UK; *Arnab Mondal*, *Ankush Bag*, Indian Institute of Technology Guwahati, India; *Martin Kuball*, University of Bristol, UK

IWGO-TuP-19 Suboxide-MBE Growth of β-Ga₂O₃ on Metallic Ru(001), *Martin Samuel Williams (Student)*, *Marco Schowalter*, *Aman Baunthiyal*, *Alexander Karg*, *Sushma Raghuvansy*, *Jens Falta*, *Andreas Rosenauer*, *Martin Eickhoff*, *Manuel Alonso-Orts*, University of Bremen, Germany

IWGO-TuP-20 Gd Incorporation in β-Ga₂O₃ Grown by Suboxide MBE: Towards Ultraviolet Emission and Luminescent Thermometry, *Martin Samuel Williams*, *Marco Schowalter*, *Alexander Karg*, *Mahmoud Elhajhasan*, University of Bremen, Germany; *Marcus Rohnke*, University of Giessen, Germany; *Carsten Ronning*, University of Jena, Germany; *Gordon Callsen*, *Andreas Rosenauer*, *Martin Eickhoff*, *Manuel Alonso-Orts*, University of Bremen, Germany

IWGO-TuP-21 Epitaxial Growth of κ(ε)-Ga₂O₃ Thin Films on 4H-SiC Substrates by Mist Chemical Vapor Deposition, *Taisei Oya*, *Kazuyuki Uno*, Wakayama University, Japan

IWGO-TuP-22 Stability and Interlayer Formation at Epitaxial p-type Oxides/Ga₂O₃ Interfaces, *Anna Sacchi*, *Michelle Smeaton*, National Laboratory of the Rockies; *Shivashree Shivamade Gowda*, University of Virginia; *Krishna Acharya*, Colorado School of Mines; *Steven R. Spurgeon*, National Laboratory of the Rockies; *Patrick Hopkins*, University of Virginia; *Vladan Stevanovic*, Colorado School of Mines; *Brooks Tellekamp*, *Andriy Zakutayev*, National Laboratory of the Rockies

IWGO-TuP-23 Structural Properties of Sn-Doped β-Ga₂O₃ Thin Films Grown on Off-Axis Sapphire Substrates by Mist Chemical Vapor Deposition, *Jae-Hyeok LIM (Student)*, *Yun-Ji SHIN*, *Tae-Yang Park*, *Seong-Min JEONG*, Korea Institute of Ceramic Engineering and Technology, Republic of Korea; *Chang-Mo KANG*, Pusan National University, Republic of Korea; *Si-Young BAE*, Pukyong National University, Republic of Korea

IWGO-TuP-24 Enhanced Surface Engineering and Deep Mesa Etching in Vertical Ru-Si-O/β-Ga₂O₃ Schottky Diodes, *Aleksandra Wojcicka (Student)*, Lukaszewicz Research Network - Institute of Microelectronics and Photonics, Poland

IWGO-TuP-25 Effect of Oxygen Ambient During Cool-Down on NiO/Ga₂O₃ Heterojunction Diodes, *Ai Ho (Student)*, *Cheng-Han Li*, *Ray-Hua Horng*, National Yang Ming Chiao Tung University (NYCU), Taiwan; *Ying-Hao Chu*, National Tsing Hua University, Taiwan

IWGO-TuP-26 Sn-Induced Defect Engineering in β-Ga₂O₃: A Combined Experimental and First-Principles Study, *Vijay Kumar Gudelli*, King Abdullah University of Science and Technology, India; *Andres E Castano Hurtado*, King Abdullah University of Science and Technology (KAUST), Colombia; *Kishor Upadhyaya*, King Abdullah University of Science and Technology (KAUST), India; *Iman S Roqan*, King Abdullah University of Science and Technology, Saudi Arabia

IWGO-TuP-27 Investigation of NiO/Ga₂O₃ Heterojunction PN Diodes by using HF Surface Treatment, *Ray Hua Horng*, National Yang Ming Chiao Tung University (NYCU), Taiwan

IWGO-TuP-28 Mechanism and Mitigation of Step-Bunching Instability in Homoepitaxial (100) β-Ga₂O₃ Thin Films, *Ta-Shun Chou*, *Saud Bin Anooz*, *Zbigniew Galazka*, *Jana Rehm*, *Arub Akhtar*, *Martin Albrecht*, *Andreas Fiedler*, *Andreas Popp*, Leibniz Institute for Crystal Growth, Germany

IWGO-TuP-29 α -Ga₂O₃ Thin Film Grown on Micropatterned Sapphire Substrate, **Kotaro Etokoro (Student)**, Kyoto University, Japan; *Takeru Wakamatsu, Yuki Isobe*, Kyoto University, Japan; *Kentaro Kaneko*, Ritsumeikan university, Japan; *Katsuhisa Tanaka*, Kyoto University, Japan

IWGO-TuP-30 Stabilization of Rutile GeO₂ on R- and M-Plane Al₂O₃ by Plasma-Assisted Molecular Beam Epitaxy, **Alexander Karg**, *Satjawoot Phiw-Ondee, Manuel Alonso-Orts, Martin Samuel Williams, Marco Schowalter, Andreas Rosenauer, Martin Eickhoff*, University of Bremen, Germany; *Patrick Vogt*, Paul-Drude-Institut für Festkörperelektronik Leibniz-Institut im Forschungsverbund Berlin, Germany

IWGO-TuP-31 Deep-Etch Mesa Edge Termination for β -Ga₂O₃ Schottky Barrier Diodes, **Charlotte Conway (Student)**, *Aditya K Bhat, Sai Charan Vanjari*, University of Bristol, UK; *Jacob Mitchell, Jay Burnett, Kerry Roberts, Huma Ashraf*, KLA Corporation UK Ltd, UK; *Matthew Smith, Xiao Tang, Martin Kuball*, University of Bristol, UK

IWGO-TuP-32 Plasma-Assisted MBE of β -Ga₂O₃/NiO Heterojunctions, *Andy Séguret*, Université Grenoble-Alpes, CEA, Grenoble INP, IRIG, PHELIQS, France; *Marty Volant*, Université Grenoble-Alpes, CEA, IRIG, MEM, France; *Fabien Jourdan*, Université Grenoble-Alpes, CEA, Grenoble INP, IRIG, PHELIQS, France; *Yann Genuist*, Université Grenoble-Alpes, CNRS, Grenoble INP, Institut Néel, France; *Hervé Roussel*, Université Grenoble Alpes, CNRS, Grenoble INP, LMGP, France; *Hanako Okuno*, Université Grenoble-Alpes, CEA, IRIG, MEM, France; *Eirini sarigiannidou*, Université Grenoble Alpes, CNRS, Grenoble INP, LMGP, France; *Vincent Consonni*, 2. Université Grenoble Alpes, CNRS, Grenoble INP, LMGP, France; *Eva Monroy, Julien Bosch*, Université Grenoble-Alpes, CEA, Grenoble INP, IRIG, PHELIQS, France

IWGO-TuP-33 Long-Term Performance of Gallium Oxide-Based Hydrogen Sensors at 600C, **William Callahan**, National Laboratory of the Rockies; *Kingsley Egbo*, Headway Technologies; *Anna Sacchi, Davi Febba*, National Laboratory of the Rockies; *Anna Staerz, Ryan O'Hayre*, Colorado School of Mines; *Brooks Tellekamp, Andriy Zakutayev*, National Laboratory of the Rockies

IWGO-TuP-34 Investigation of the Effect of Heated-H₃PO₄ on Fin Sidewall Roughness and Electrical Performance, **Xin Zhai (Student)**, University of Michigan, Ann Arbor; *Jay Burnett, Kerry Roberts*, KLA-Tencor, UK; *Edward Walsby*, KLA-Tencor; *Huma Ashraf*, KLA-Tencor, UK; *Rebecca Peterson*, University of Michigan, Ann Arbor; *Elaheh Ahmadi*, University of California Santa Barbara

IWGO-TuP-35 Band Alignment of NiO_x/ β -Ga₂O₃(001) Heterojunction Consistently Determined by I-V, C-V, and IPE Measurements, **Akihira Munakata (Student)**, University of Tokyo, Japan; *Hiranobu Miyamoto, Kohei Sasaki*, Novel Crystal Technology, Inc., Japan; *Takuya Maeda*, University of Tokyo, Japan

IWGO-TuP-36 Aln Mesa Sidewall Passivation Enables Thermally Stable Reverse Blocking in Vertical β -Ga₂O₃ Power Diodes, **Ganesh Mainali (Student)**, *Nuzhat Yousf*, King Abdullah University Of Science and Technology, Saudi Arabia; *Dhanu Chettri, Haicheng Cao, Leo Raj Solay*, King Abdullah University Of Science, Saudi Arabia; *Xiaohang Li*, King Abdullah University Of Science and Technology, Saudi Arabia

IWGO-TuP-37 Deep-Acceptor-Mediated Inversion Enabling Normally-Off β -Ga₂O₃ MOSFETs without Epitaxy, **Sarit Dhar**, *Tamara Isaacs-Smith*, Auburn University; *Jacob Lawson, Charles Ebbing, Chase Kitzmiller, Joseph Merrit*, Air Force Research Laboratory, USA

IWGO-TuP-38 Achievement of SiO₂/ β -Ga₂O₃ (001) MOS Interface with Low in Terface State Density by Employing ALD with O₃ as an Oxidant and Low-temperature (600°C) Post-deposition Annealing, **Atsushi Tamura**, *Hayama Imaida, Koji Kita*, University of Tokyo, Japan

IWGO-TuP-39 Gallium Oxide-Based Photonic Memory Transistor for Nonvolatile Optoelectronic Applications, **Jiatong Dong (Student)**, King Abdullah University of Science and Technology, China; *Iman Roqan*, King Abdullah University of Science and Technology, Saudi Arabia

IWGO-TuP-40 Vertical Trench-Mos Barrier Diode on (001) β -Ga₂O₃ with Trench Formation by Hot H₃PO₄ Treatment, **Aaron Adams**, KBR/AFRL

IWGO-TuP-41 Challenges and Solutions in Mist-CVD of Ga₂O₃ Heteroepitaxial Films, **Roman Yatskiv**, Institute of Photonics and Electronics of the Czech Academy of Sciences, Czechia

Wednesday Morning, August 5, 2026

Room ESJ 0202		
8:00am	BREAKFAST	International Workshop on Gallium Oxide and Related Materials (IWGO-6) Session IWGO-WeM1 Plenary Session II Moderators: Huili (Grace) Xing , Cornell University, Martin Albrecht , Leibniz Institute for Crystal Growth, Germany
8:45am	PLENARY: IWGO-WeM1-10 From Crystal Growth to Power Devices: The Evolution of Gallium Oxide Technology, <i>Kohei Sasaki</i> , Novel Crystal Technology, Inc., Japan	
9:30am	INVITED: IWGO-WeM1-19 Homoepitaxial Growth of β -Ga ₂ O ₃ Using HVPE and MOVPE, <i>Yoshinao Kumagai</i> , Tokyo University of Agriculture and Technology, Japan	
9:55am	INVITED: IWGO-WeM1-24 Characterization of Shallow and Deep Level Defects in β -(Al _x Ga _{1-x}) ₂ O ₃ Bulk Crystals, <i>Andreas Fiedler</i> , Leibniz-Institut für Kristallzüchtung, Germany	
10:20am	COFFEE BREAK	
10:50am	IWGO-WeM2-35 Structural and Electrical Properties of <i>c</i> -plane α -Ga ₂ O ₃ Grown on High-quality α -Cr ₂ O ₃ Templates by HVPE, <i>Yuichi Oshima, Takayoshi Oshima</i> , National Institute for Materials Science, Japan; <i>Shiyu Xiao, Kazuto Murakami, Katsuhiko Imai, Takahiro Tomita</i> , NGK INSULATORS, LTD, Japan	International Workshop on Gallium Oxide and Related Materials (IWGO-6) Session IWGO-WeM2 Epitaxial Growth and Doping Control II Moderators: Ahmad Islam , AFRL, Sriram Krishnamoorthy , University of California Santa Barbara
11:05am	IWGO-WeM2-38 Homoepitaxial Growth on (0-1-1) β -Ga ₂ O ₃ Substrates Using Oxide Vapor Phase Epitaxy, <i>Tomoka Nishikawa (Student)</i> , The University of Osaka, Japan; <i>Chia-Hung Lin, Kohei Sasaki, Akito Kuramata</i> , Novel Crystal Technology, Inc., Japan; <i>Eisho Kishimoto, Tomoyuki Tanikawa, Ryuji Katayama, Shigeoyoshi Usami, Masayuki Imanishi, Yusuke Mori</i> , The University of Osaka, Japan	
11:20am	IWGO-WeM2-41 Fe Compensation Doping and Interface Stability for Mitigating Interfacial Si Conductivity in MBE-Grown β -Ga ₂ O ₃ Thin Films, <i>Brenton Noesges, Prescott Evans, Jian Li, Core4ce; Mark Gordon</i> , University of Dayton; <i>Daram Ramdin, Core4ce; Nicholas Sepelak</i> , KBR; <i>Daniel Dryden</i> , Air Force Research Lab, Sensors Directorate; <i>Shin Mou, Adam Neal, Thaddeus Asel</i> , Air Force Research Laboratory, Materials and Manufacturing Directorate	
11:35am	IWGO-WeM2-44 Coherent Growth of α -(Al,Ga) ₂ O ₃ on α -Cr ₂ O ₃ Templates by Mist-CVD, <i>Riena Jinno</i> , The University of Tokyo, Japan; <i>Shiyu Xiao</i> , NGK Insulators, Ltd, Japan; <i>Takayoshi Oshima</i> , NIMS (National Institute for Materials Science), Japan; <i>Satoshi Iwamoto</i> , The University of Tokyo, Japan; <i>Kazuto Murakami</i> , NGK Insulators, Ltd., Japan; <i>Katsuhiko Imai, Takahiro Tomita</i> , NGK Insulators, Ltd, Japan	
11:50am	IWGO-WeM2-47 Demonstration of Homojunction Ga ₂ O ₃ PiN Diodes with High Bipolar Injection, <i>Pierre Gallarday (Student)</i> , <i>Aniol Vellvehí, Miquel Vellvehí, José Rebollo, Josep Montserrat</i> , INSTITUTE OF MICROELECTRONICS OF BARCELONA - (IMB-CNM-CSIC), Spain; <i>Corine Sartel, Yves Dumont, Ekaterine Chikoizde</i> , Groupe d'étude de la matière condensée (GEMaC) - UVSQ, France; <i>Amador Pérez-Tomás</i> , INSTITUTE OF MICROELECTRONICS OF BARCELONA - (IMB-CNM-CSIC), Spain	
12:05pm	IWGO-WeM2-50 Uniform Growth of Thick Homoepitaxial β -Ga ₂ O ₃ Layers on 2-inch (010) Substrates by Low-Pressure Hot-Wall MOVPE, <i>Yoshiki Iba (Student)</i> , <i>Yuma Terauchi</i> , Tokyo University of Agriculture and Technology, Japan; <i>Junya Yoshinaga</i> , TAIYO NIPPON SANSO CORPORATION, Japan; <i>Yasuhiro Hashimoto</i> , Sumitomo Metal Mining Co. Ltd., Japan; <i>Yoshinao Kumagai</i> , Tokyo University of Agriculture and Technology, Japan	

Wednesday Afternoon, August 5, 2026

International Workshop on Gallium Oxide and Related Materials (IWGO-6) Room ESJ 0202 - Session IWGO-WeA Advanced Device Scaling and Fabrication Techniques I Moderators: Siddarth Rajan, The Ohio State University, Yuhao Zhang, University of Hong Kong	
2:00pm	INVITED: IWGO-WeA-1 Recent Advances in β -Ga ₂ O ₃ Power and RF Device Technologies, Uttam Singiseti , University at Buffalo
2:25pm	IWGO-WeA-6 1.5 kV/0.6 A Double Pulse Test Switching Of Cr ₂ O ₃ / β -Ga ₂ O ₃ Heterojunction Diodes With > 3 kV Breakdown Voltages And Record Low Reverse Recovery Charge, Chinmoy Nath Saha , University of California Santa Barbara; Yuzhou Yao, Juchen Yang , The Ohio State University; Yizheng Liu , University of California at Santa Barbara; Pengyu Fu, Shuwei He , The Ohio State University; James S. Speck , University of California at Santa Barbara; Jin Wang , The Ohio State University; Sriram Krishnamoorthy , University of California at Santa Barbara
2:40pm	IWGO-WeA-9 Sub-Micron β -Ga ₂ O ₃ FinFETs with >700 mA/mm Current Density and >10 ⁸ ON/OFF Ratio Using Si δ -Doped Channels, Nabasindhu Das (Student) , Arizona State University
2:55pm	IWGO-WeA-12 Over 3 kV Ultra-low Leakage Vertical (011) β -Ga ₂ O ₃ Diodes with Schottky Contact Engineering and High- κ Field Plate, Emerson Hollar (Student) , Esmat Farzana , Iowa State University
3:10pm	IWGO-WeA-15 Vertical Ga ₂ O ₃ (010) FinFETs Processed with Nitrogen Radical Irradiation, Zhenwei Wang , National Institute of Information and Communications Technology, Japan; Jin Inajima, Kohki Tsujimoto, Yusuke Teramura , Osaka Metropolitan University, Japan; Yoshiki Iba, Yuma Terauchi , Tokyo University of Agriculture and Technology, Japan; Junya Yoshinaga , Tokyo University of Agriculture and Technology/TAIYO NIPPON SANSO CORPORATION, Japan; Takafumi Kamimura , National Institute of Information and Communications Technology, Japan; Yoshinao Kumagai , Tokyo University of Agriculture and Technology, Japan; Masataka Higashiwaki , Osaka Metropolitan University/NICT, Japan
3:25pm	IWGO-WeA-18 Enhancement-Mode Ga ₂ O ₃ CAVETs with Improved Breakdown Voltage by Hot Implantation, Jun Morihara (Student) , Osaka Metropolitan University, Japan; Daisuke Matsuo, Shun Konno, Kosuke Usui, Shinya Takemura , Nissin Ion Equipment Co., Ltd., Japan; Zhenwei Wang , National Institute of Information and Communications Technology, Japan; Romualdo Ferreyra , Osaka Metropolitan University, Japan; Kohei Tanaka , Nissin Ion Equipment Co., Ltd., Japan; Masataka Higashiwaki , Osaka Metropolitan University, Japan
3:40pm	IWGO-WeA-21 Enhancement-Mode Vertical β -Ga ₂ O ₃ U-Trench MOSFET with N-doped CBL and MOCVD regrown n ⁺ Contact Layers, Walid Amir, Jiawei Liu, Surajit Chakraborty , University at Buffalo-SUNY; Dongsu Yu, Md. Mosarof Hossain Sarkar, Hingping Zhao , Ohio State University; Uttam Singiseti , University at Buffalo-SUNY

International Workshop on Gallium Oxide and Related Materials (IWGO-6)

Room Concourse - Session IWGO-WeP

IWGO Poster Session III

4:00 – 6:00 pm

Moderators:

Hari Nair, Cornell University,

Saurav Roy, North Carolina State University

IWGO-WeP-1 Ultra-Sensitive Arc-Detecting DUV Sensor based on p-NiO/ β -Ga₂O₃ Heterojunction Using p+ NiO Interlayer, **Taejun Park**, Yusup Jung, Sanghun Kim, TaiYoung Kang, SinSu Kyoung, Powercubesemi, Inc., Republic of Korea

IWGO-WeP-2 Electrical Characterization of Mist-CVD HfO_x/ β -Ga₂O₃ MIS Capacitor, **Hayato Tanikawa (Student)**, Kyoto Institute of Technology, Japan; Kazutaka Kanegae, Hiroyuki Nishinaka, Kyoto Institute of Technology, Japan

IWGO-WeP-3 Tuning the Conductivity of p-type Ni_{1-x}O Thin Films for Ni_{1-x}O/ β -Ga₂O₃ Heterojunction Power Devices, **Thomas Ribault (Student)**, Akash Patnaik, Bruno Berini, Corinne Sartel, CNRS-UVSQ, France; Yunlin Zheng, Jean-Louis Cantin, CNRS-INSP, France; Zurab Kushitashvili, Amiran Bibilashvili, Institute of Nano et Microelectronics, Tbilisi, Georgia; Tom Micottis, Farid Medjdoub, CNRS-I.E.M.N., France; Ekaterine Chikoidze, Yves Dumont, CNRS-UVSQ, France

IWGO-WeP-4 Electro-Optical Metrology Development to Probe Deep-Level Traps in β -Ga₂O₃ MOSFETs, **Ory Maimon**, George Mason University; Neil Moser, Air Force Research Laboratory; Pragna Shrestha, Min-Yeong Kim, National Institute for Science and Technology (NIST); Sang-Mo Koo, Kwangwoon University, Republic of Korea; Kyle Liddy, Andrew Green, Kelson Chabak, Air Force Research Laboratory; Qiliang Li, George Mason University; Sujitra Pookpanratana, National Institute for Science and Technology (NIST)

IWGO-WeP-5 The Morphology of the Cr₂O₃ Films Surfaces Analyzed by Multifractal Formalism, **Pavel Butenko**, Ioffe Institute, Russian Federation

IWGO-WeP-6 Growth of 2-inch n-type β -Ga₂O₃ (011) Single Crystal by the VB Method, **Yuki Ueda**, Takuya Igarashi, Kimiyoshi Koshi, Sho Hasegawa, Ryoichi Sakaguchi, Taiki Chujo, Ryo Shinagawa, Kohei Sasaki, Akito Kuramata, Novel Crystal Technology, Inc., Japan

IWGO-WeP-7 c-In₂O₃ Growth by Oxide Vapor Phase Epitaxy Using In₂O and H₂O Source Gases, **Rie Togashi**, Takumi Shimazaki, Sophia University, Japan; Masato Ishikawa, Gas-Phase Growth Ltd., Japan

IWGO-WeP-8 Fabrication and Characterization of (011)-Oriented Substrates by the Vertical Bridgman Method, **Dong-Jun Lee**, Jinki Kang, AXEL, Republic of Korea

IWGO-WeP-9 Characterization of p-Cr₂O₃/n-Ga₂O₃ Heterojunction Rectifiers, **Hannah Masten**, Frank Kelly, National Research Council; Chinmoy Nath Saha, Yizheng Liu, University of California at Santa Barbara; Tia Gray, National Research Council; Sriram Krishnamoorthy, University of California at Santa Barbara; Marko Tadjer, Naval Research Laboratory

IWGO-WeP-10 Temperature Dependent Hall as a Probe for Parasitic Conduction in Gallium Oxide Epitaxial Structures, **Joshua Buontempo (Student)**, Cameron Gorsak, Pushpanshu Tripathi, Hari Nair, Cornell University

IWGO-WeP-11 3D Modeling of EFG β -Ga₂O₃ Crystal Growth: Effect of Process on Crystal Quality, **Alex Galyukov**, STR US, Inc.; Aleksa Crnobrnja, Andrey Smirnov, STR Europe, Serbia

IWGO-WeP-12 Multi-Ribbon Growth of Offcut (100) β -Ga₂O₃ by EFG, **Kurt Lindquist**, David Joyce, Kale Geddis, Drew Haven, Luxium Solutions, LLC; Robert Lavelle, Luke Lyle, Benjamin Dutton, Penn State University

IWGO-WeP-13 Development of Surface Preparation Methods for Insulating and Conductive, Miscut (100) β -Ga₂O₃ Substrates, **Robert Lavelle**, Luke Lyle, Benjamin Dutton, Connor Beakes, Eric Welp, Scott Pistner, Andrew Balog, Penn State University; Drew Haven, David Joyce, Luxium Solutions; Nasim Alem, Joan Redwing, David Snyder, Penn State University

IWGO-WeP-14 Composition-Dependent Thermal Conductivity of Ge_xSn_{1-x}O₂ Alloys, **Xiao Zhang**, Emmanouil Kioupakis, University of Michigan, Ann Arbor

IWGO-WeP-15 MOCVD Growth and Characterization of β -Ga₂O₃ Field Effect Transistors Grown on 2" (010) Substrates, **Will Brand**, Fikadu Alema, Agnitron Technology; Austin Hickman, Soctera; Andrei Osinsky, Agnitron Technology

IWGO-WeP-16 DRCLS Defects Near LiGa₅O₈/Ga₂O₃ Heterointerfaces, **Carlos DeLeon (Student)**, Kaitian Zhang, Hongping Zhao, Leonard Brillson, Ohio State University

IWGO-WeP-17 Electric-Field-Limited Breakdown in Oxide/ β -Ga₂O₃ p-n Heterojunction Diodes, **Sanjay Gopalan**, John Muth, Ki Wook Kim, North Carolina State University

IWGO-WeP-18 Hot-wall MOCVD Growth on Miscut (100) β -Ga₂O₃ Substrates, **Benjamin Dutton**, Robert Lavelle, Luke Lyle, Randal Cavaleiro, Connor Beakes, Scott Pistner, Penn State University Applied Research Laboratory; Drew Haven, David Joyce, Luxium Solutions LLC; David Snyder, Penn State University Applied Research Laboratory

IWGO-WeP-19 Temperature-Optimized Lattice-Matched Epitaxy of UWBG Rutile Ge_xSn_{1-x}O₂ on (001) Rutile TiO₂, **Satyam Patel (Student)**, Becky (R.L.) Peterson, University of Michigan, Ann Arbor

IWGO-WeP-20 Growth of Rutile-Type GeO₂ by Oxide Vapor Phase Epitaxy, **Haru Nakano (Student)**, Shigeyoshi Usami, Masayuki Imanishi, Yusuke Mori, Osaka University, Japan

IWGO-WeP-21 Thermodynamic analysis of GeO₂ growth via Oxide Vapor Phase Epitaxy, **Shigeyoshi Usami**, Masayuki Imanishi, Yusuke Mori, The University of Osaka, Japan

IWGO-WeP-22 Experimental Study of Hf-Doped β -Ga₂O₃ by Floating Zone Method, **Myeonggyun Kang (Student)**, Tohoku University, Japan, Republic of Korea; Kei Kamada, Hisato Suezumi, Masanori Kitahara, Satoshi Ishizawa, Rikito Murakami, Yuui Yokota, Masao Yoshino, Akira Yoshikawa, Tohoku University, Japan

IWGO-WeP-23 Exploration of Conductivity-Type Control in β -Ga₂O₃ through Nitrogen Doping, **Haizhong Zhang**, Fuzhou University, China

IWGO-WeP-24 Re-Growth on Multi-Directional Fin Structures of (001) β -Ga₂O₃, **Sai Kkrishna Anandan (Student)**, Min-Yeong Kim, Arpit Nandi, Martin Kuball, University of Bristol, UK

IWGO-WeP-25 Surface Termination and Structural Stability of β -(Al_xGa_{1-x})₂O₃ (100) (X = 0 ~ 0.3) as-Cleaved Single Crystals, **Ming-Chao Kao (Student)**, Deutsches Elektronen-Synchrotron DESY (NanoLab), Germany

IWGO-WeP-26 Effect of the GaN Surface on n-Ga₂O₃/p-GaN Heterointerface Quality, **Daniel Pennachio**, US Naval Research Laboratory; Frank Kelly, Katie Gann, National Research Council Postdoctoral Fellow, residing at NRL; Emma Rocco, Michael Mastro, US Naval Research Laboratory

IWGO-WeP-27 p-GaN/n-Ga₂O₃ Diodes via MOCVD Selective Area Growth, **Frank Kelly**, Emma Rocco, Daniel Pennachio, James Lundh, Alan Jacobs, Tolen Nelson, Marko Tadjer, Michael Mastro, Naval Research Laboratory

IWGO-WeP-28 Performance of MOCVD Grown Schottky Barrier Diodes with a Graded β -(Al,Ga)₂O₃ Cap, **Cameron Gorsak**, Frank Kelly, Jenifer Hajzus, Daniel Pennachio, Naval Research Laboratory; Katie Gann, Naval Research Laboratory, USA; Alan Jacobs, Emma Rocco, Michael Mastro, Naval Research Laboratory

IWGO-WeP-29 Vertical β -Ga₂O₃ U-Trench MOSFETs With N-ion-implanted Current Blocking Layer and Implanted Source, **Jiawei Liu (Student)**, Surajit Chakraborty, Walid Amir, Uttam Singiseti, University at Buffalo-SUNY

IWGO-WeP-30 Donor Doping of β -Ga₂O₃ by Cl Ion Implantation, **Katie Gann**, Alan Jacobs, Frank Kelly, Emma Rocco, Cameron Gorsak, Marko Tadjer, Naval Research Laboratory; Rachael Myers-Ward, naval research Laboratory; Karl Hobart, Michael Mastro, Naval Research Laboratory

IWGO-WeP-31 Thermodynamic analysis of (Al_xGa_{1-x})₂O₃ MOCVD growth with TMA, O₂, and TMG and TEG as Ga precursors, **Andri Dhora (Student)**, Lund University, Sweden

IWGO-WeP-32 Effect of Ga Etching and Wet Acid Treatments on MOS Characteristics for Vertical β -Ga₂O₃ Power Devices, **Akhila Mattapalli (Student)**, Chinmoy Nath Saha, University of California at Santa Barbara; Carl Peterson, Steve Rebollo, Jim Speck, Sriram Krishnamoorthy, University of California Santa Barbara

IWGO-WeP-33 High-Temperature Stability of Contacts to β -Ga₂O₃, **Donivan R. Mouch (Student)**, The Applied Research Lab at The Pennsylvania State University; Paul Kelemen, Sohyun Lee, Nathan S. Banner, Chan-Wen Chiu, Suzanne E. Mohney, Pennsylvania State University; Luke A. M. Lyle, The Applied Research Lab at The Pennsylvania State University

IWGO-WeP-34 Investigation of Temperature-Dependent Forward Transport Mechanism in kV class NiO/ β -Ga₂O₃ Heterojunction Diodes, **Surajit Chakraborty**, Deb Indronil Sajib, Uttam Singiseti, University at Buffalo-SUNY

IWGO-WeP-35 Group-III Flux Etching of β -(Al_xGa_{1-x})₂O₃ Heterostructures, **Emma Rocco**, Frank Kelly, J. S. Lundh, Daniel Pennachio, Katie Gann, Cameron Gorsak, Alan Jacobs, Marko Tadjer, Michael Mastro, U.S. Naval Research Laboratory

IWGO-WeP-36 Carrier Transport Across Wafer Bonded (001) β -Ga₂O₃ Interfaces, **Advait Gilankar (Student)**, Arizona State University; *Michael Liao, Piyush Shah*, Apex Microdevices; *Mark Goorsky*, University of California Los Angeles; *Nidhin Kalarickal*, Arizona State University

IWGO-WeP-37 High-Reflectance In-Plane Ga₂O₃/Air DBRs Fabricated by HEATE on (010) β -Ga₂O₃, **SOTARO IJIMA (Student)**, TAKAHASHI YUKI, Sophia Univ, Japan; *AKIHIKO KIKUCHI*, Sophia Univ / Sophia Semiconductor Research Institute, Japan

IWGO-WeP-38 Phase-Dependent Photoluminescence of Near-Infrared Color Centers in Ga₂O₃, **Keidai Toyoshima (Student)**, The University of Tokyo, Japan; *Mathias Marchal*, Technical University of Denmark, Denmark; *Riena Jinno, Satoshi Iwamoto*, The University of Tokyo, Japan

IWGO-WeP-39 Transmutation-doped β -Ga₂O₃ via Thermal Neutron Irradiation, **Richard Barber (Student)**, University of Missouri; *Marko Tadjer, Evan Glaser*, Naval Research Laboratory; *Marc Weber*, Washington State University; *Alison Hartman*, University of Missouri-Columbia; *Jaime Freitas, Steven Bennett, Mason Klemm, Alan Jacobs, Karl Hobart*, Naval Research Laboratory; *Kohei Sasaki, Akito Kuramata*, Novel Crystal Technology, Japan; *P. Shiv Halasyamani*, University of Houston; *Blaine Reid, John Brockman, John Gahl*, University of Missouri

IWGO-WeP-40 Optimizing β -Ga₂O₃ MOCVD Regrowth for Vertically Scaled Channels, **Julian Gervassi-Saga (Student)**, *Nabasinthu Das, Advait Gilankar, Nidhin Kurian Kalarickal*, School of Electrical, Computer and Energy Engineering, Arizona State University

IWGO-WeP-41 962 V Ga₂O₃ Schottky Power Diodes on (011) Substrate, **Luoyuan Jiang (Student)**, *Md Mosarof Hossain Sarkar, Yibo Xu, Hongping Zhao, Wu Lu*, Ohio State University

IWGO-WeP-42 Identifying the Origin of Emissions and Anisotropic Properties of Different Crystallographic Orientation Sn-Doped β -Ga₂O₃ Substrates, **Kishor Upadhyaya**, King Abdullah University of Science and Technology, India; *Andres Hurtado*, King Abdullah University of Science and Technology, Colombia; *Hadeel Alamoudi, Iman Roqan*, King Abdullah University of Science and Technology, Saudi Arabia

IWGO 2026 Rump Session

6:00 – 8:00 pm

ESJ 0202

Moderator: **Ali Sayir**, Air Force Office of Scientific Research

PANELISTS:

- **John Frank**, Luxium Solutions
- **Andrew Green**, AFRL
- **Masataka Higashiwaki**, Osaka Metropolitan University/National Institute of Information and Communications Technology
- **Fritz Kub**, US Naval Research Laboratory
- **Akito Kuramata**, Novel Crystal Technology
- **Jon McCandless**, Gallox Semiconductors
- **Lynn Petersen**, Office of Naval Research
- **Victor Veliadis**, Power America; NC State
- **Man-Hoi Wong**, Hong Kong University of Science and Technology

Thursday Morning, August 6, 2026

Room ESJ 0202		
8:00am	BREAKFAST	International Workshop on Gallium Oxide and Related Materials (IWGO-6) Session IWGO-ThM1 Theory, Modeling, and Simulation Moderators: Jinwoo Hwang , The Ohio State University, Joel Varley , Lawrence Livermore National Laboratory
8:30am	INVITED: IWGO-ThM1-7 Impact of Defects and Impurities on the Properties of Al ₂ O ₃ , <i>Chris G. van de Walle</i> , UCSB	
8:55am	INVITED: IWGO-ThM1-12 GeO ₂ and Ge _x Sn _{1-x} O ₂ Alloys: Emerging Ultra-Wide-Band-Gap Materials for Power Electronics, <i>Emmanouil (Manos) Kioupakis</i> , University of Michigan, Ann Arbor	
9:20am	IWGO-ThM1-17 Rutile Ge _x Sn _{1-x} O ₂ Alloys for Ultra-Wide Bandgap Electronics: Phase Stability and Bandgap Engineering, <i>Alp Kurbay (Student)</i> , University of Michigan, Ann Arbor; <i>Yann Müller</i> , EPFL, Switzerland; <i>Xiao Zhang</i> , University of Michigan, Ann Arbor; <i>Anirudh Natarajan</i> , EPFL, Switzerland; <i>Emmanouil Kioupakis</i> , University of Michigan, Ann Arbor	
9:35am	IWGO-ThM1-20 Single Ga-Layer Reconstruction Mediates Ga ₂ O ₃ Heteroepitaxy: A Multiscale Atomistic Study, <i>Ilaria Bertoni (Student)</i> , <i>Aldo Ugolotti</i> , <i>Anna Marzegalli</i> , Università degli Studi di Milano-Bicocca, Italy; <i>Flyura Djurabekova</i> , University of Helsinki, Finland; <i>Leonida Miglio</i> , Università degli Studi di Milano-Bicocca, Italy	
9:50am	IWGO-ThM1-23 Carrier Mobility in Ge _x Sn _{1-x} O ₂ Alloys from First Principles, <i>Amanda Wang (Student)</i> , <i>Alp Kurbay</i> , <i>Xiao Zhang</i> , <i>Nick Pant</i> , <i>Emmanouil Kioupakis</i> , University of Michigan	
10:05am	IWGO-ThM1-26 Refractive Indices, Band-to-Band Transitions, and Ultraviolet Dielectric Functions of Unintentionally-Doped ($x = 0 \dots 0.3$) and Silicon Doped ($x = 0 \dots 0.25$) Single Crystal (100) β -(Al _x Ga _{1-x}) ₂ O ₃ , <i>Preston Sorensen (Student)</i> , University of Nebraska - Lincoln; <i>Alyssa Mock</i> , Weber State University; <i>Megan Stokey</i> , Milwaukee School of Engineering; <i>Ufuk Kilic</i> , University of Nebraska - Lincoln; <i>Rafal Korlacki</i> , J. A. Woollam Co., Inc.; <i>Akhil Mauze</i> , <i>Yuewei Zhang</i> , <i>James Speck</i> , University of California Santa Barbara; <i>Zbigniew Galazka</i> , Leibniz Institute for Crystal Growth, Germany; <i>Vanya Darakchieva</i> , Lund University, Sweden; <i>Mathias Schubert</i> , University of Nebraska - Lincoln	
10:20am	COFFEE BREAK	
10:50am	INVITED: IWGO-ThM2-35 4D-STEM and Machine Learning Investigation of Defects and Polymorphism in Ultra Wide Band Gap Oxides and Nitrides, <i>Jinwoo Hwang</i> , The Ohio State University	International Workshop on Gallium Oxide and Related Materials (IWGO-6) Session IWGO-ThM2 Defects Science IV Moderators: Emma Rocco , Naval Research Laboratory, Chris G. van de Walle , University of California Santa Barbara
11:15am	IWGO-ThM2-40 Bandgap Renormalization in Si-doped β -Ga ₂ O ₃ Films, <i>Takeyoshi Onuma</i> , <i>Kai Yamamoto</i> , <i>Kyohei Tanaka</i> , Kogakuin University, Japan; <i>Yoshiki Iba</i> , Tokyo University of Agriculture and Technology, Japan; <i>Junya Yoshinaga</i> , TAIYO NIPPON SANSO CORPORATION, Japan; <i>Yuma Terauchi</i> , Tokyo University of Agriculture and Technology, Japan; <i>Tomohiro Yamaguchi</i> , Kogakuin University, Japan; <i>Masataka Higashiwaki</i> , Osaka Metropolitan University/NICT, Japan; <i>Yuzaburo Ban</i> , TAIYO NIPPON SANSO ATI CORPORATION, Japan; <i>Yoshinoo Kumagai</i> , Tokyo University of Agriculture and Technology, Japan; <i>Tohru Honda</i> , Kogakuin University, Japan	
11:30am	IWGO-ThM2-43 Formation and Stabilization of Ga Vacancies in β -(Al,Ga) ₂ O ₃ : Effects of Al-alloying, Si-doping, and Proton Irradiation, <i>Luliia Zhelezova (Student)</i> , <i>Ilja Makkonen</i> , University of Helsinki, Finland; <i>Zbigniew Galazka</i> , Leibniz-Institut für Kristallzüchtung, Germany; <i>Filip Tuomisto</i> , University of Helsinki, Finland	
11:45am	IWGO-ThM2-46 Nitrogen-Doped (AlGa) ₂ O ₃ /n-Ga ₂ O ₃ Junctions Grown by Plasma-Assisted Molecular Beam Epitaxy, <i>Kohki Tsujimoto (Student)</i> , <i>Toshiki Nakaoka</i> , <i>Yusuke Teramura</i> , <i>Shoma Takeda</i> , <i>Satoko Honda</i> , <i>Masataka Higashiwaki</i> , Osaka Metropolitan University, Japan	

Friday Morning, August 7, 2026

Room ESJ 0202		
8:00am	BREAKFAST	International Workshop on Gallium Oxide and Related Materials (IWGO-6) Session IWGO-FrM1 Plenary Session III Moderators: Hongping Zhao , The Ohio State University, Shizuo Fujita , Kyoto University, Japan
8:45am	PLENARY: IWGO-FrM1-10 Scaling Ga ₂ O ₃ Power Electronics: From 10 kV Devices to Megawatt Modules, <i>Yuhao Zhang</i> , The University of Hong Kong	
9:30am	INVITED: IWGO-FrM1-19 Formation of High-Quality SiO ₂ /β-Ga ₂ O ₃ MOS Structures: Design and Optimization of Post-Annealing Processes, <i>Heiji Watanabe, Kensei Maeda, Masahiro Hara, Takuma Kobayashi</i> , The University of Osaka, Japan	
9:55am	IWGO-FrM1-24 Analysis of Packaged Ga ₂ O ₃ Schottky Barrier Diodes (SBDs) for AC Rectification at Industrial Voltages, <i>Jeremiah Williams</i> , KBR Inc.; <i>Nolan Hendricks, Joshua Piel</i> , AFRL; <i>Zachary Weber</i> , Ohio State University; <i>Aaron Adams, Weisong Wang</i> , KBR Inc.; <i>Kyle Liddy, Daniel Dryden</i> , AFRL; <i>Takekazu Masui, Higuchi Mitsuhito</i> , NCT, Japan; <i>Ahmad Islam, Andrew Green</i> , AFRL	
10:10am	IWGO-FrM1-27 2.2 kV NiO Based JTE β-Ga ₂ O ₃ Schottky Barrier Diode with Improved Reliability under High-Temperature Storage Stress, <i>Junpeng Wen (Student)</i> , <i>Xuanze Zhou, Guangwei Xu, Shibing Long</i> , University of Science and Technology of China	
10:25am	IWGO-FrM1-30 >1 GW/cm ² β-Ga ₂ O ₃ NiO _x Heterojunction Diodes on MOCVD-Grown (110) and (010) Epilayers, <i>Carl Peterson (Student)</i> , <i>Yizheng Liu, Chinmoy Nath Saha</i> , University of California Santa Barbara; <i>Jacob H. Leach</i> , Kyma Technologies Inc.; <i>James S. Speck, Sriram Krishnamoorthy</i> , University of California Santa Barbara	
10:40am	COFFEE BREAK	
11:10am	INVITED: IWGO-FrM2-39 High-Performance β-Ga ₂ O ₃ Vertical Diodes and FinFETs with High Electric Field Strength, <i>Sriram Krishnamoorthy</i> , University of California at Santa Barbara	International Workshop on Gallium Oxide and Related Materials (IWGO-6) Session IWGO-FrM2 Advanced Device Scaling and Fabrication Techniques II Moderators: Samuel Graham , University of Maryland College Park, Uttam Singiseti , University of Buffalo
11:35am	IWGO-FrM2-44 Diffusion Suppression of Mg and High Performance β-Ga ₂ O ₃ Current Blocking Layers by N+Mg Co-Doping Approach, <i>Fenfen Fenda Florena, Hironobu Miyamoto, Yuki Koishikawa, Hirofumi Shinohara, Kohei Sasaki, Akito Kuramata</i> , NCT, Japan	
11:50am	IWGO-FrM2-47 >3.3 kV Ga ₂ O ₃ Monolithic Bidirectional Switch: Impact of NiO/Ga ₂ O ₃ Interface Charges, <i>Yuan Qin</i> , Virginia Tech; <i>Yuhao Zhang</i> , The University of Hong Kong, China	
12:05pm	Closing Remarks	

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